

WEST Search History

DATE: Tuesday, September 30, 2003

<u>Set Name</u> side by side	<u>Query</u>	<u>Hit Count</u>	<u>Set Name</u> result set
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DB=USPT,PGPB,JPAB,EPAB,DWPI,TDBD; PLUR=YES; OP=OR

L2	L1 same periphery	24	L2
L1	(silicon near2 crystal) same osf!	191	L1

END OF SEARCH HISTORY

WEST

Generate Collection

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L2: Entry 23 of 24

File: DWPI

Jul 27, 1999

DERWENT-ACC-NO: 1999-473951
DERWENT-WEEK: 199940
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TITLE: Crystal growth for manufacturing quality wafer - involves drawing at a velocity so oxidation induced stacking fault ring is generated inwardly from crystal periphery or may quench in the crystal centre part

PATENT-ASSIGNEE:

ASSIGNEE

CODE

SUMITOMO METAL IND LTD

SUMQ

PRIORITY-DATA: 1997JP-0367703 (December 26, 1997)

PATENT-FAMILY:

PUB-NO	PUB-DATE	LANGUAGE	PAGES	MAIN-IPC
JP 11199385 A	July 27, 1999		005	C30B029/06

APPLICATION-DATA:

PUB-NO	APPL-DATE	APPL-NO	DESCRIPTOR
JP 11199385A	December 26, 1997	1997JP-0367703	

INT-CL (IPC): C30 B 15/00; C30 B 29/06

ABSTRACTED-PUB-NO: JP 11199385A
BASIC-ABSTRACT:

NOVELTY - Quenching near the solid-liquid boundary surface of the single crystal (11) is carried out during the growth of silicon single crystal by Czochralski process. The drawing velocity of the single crystal is such that the OSF (oxidation induced stacking fault) ring is generated inwardly from crystal periphery or it may quench in the crystal centre part.

USE - For manufacturing quality wafer.

ADVANTAGE - Yield of production is high and generation of porosity cluster is suppressed.

DESCRIPTION OF DRAWING(S) - The figure shows drawing of single crystal. (11) Single crystal.

CHOSEN-DRAWING: Dwg.1/1

TITLE-TERMS: CRYSTAL GROWTH MANUFACTURE QUALITY WAFER DRAW VELOCITY SO OXIDATION INDUCE STACK FAULT RING GENERATE INWARD CRYSTAL PERIPHERAL QUENCH CRYSTAL CENTRE PART

DERWENT-CLASS: L03 U11

CPI-CODES: L04-B01;

EPI-CODES: U11-B01;

SECONDARY-ACC-NO:

CPI Secondary Accession Numbers: C1999-139450

Non-CPI Secondary Accession Numbers: N1999-354450